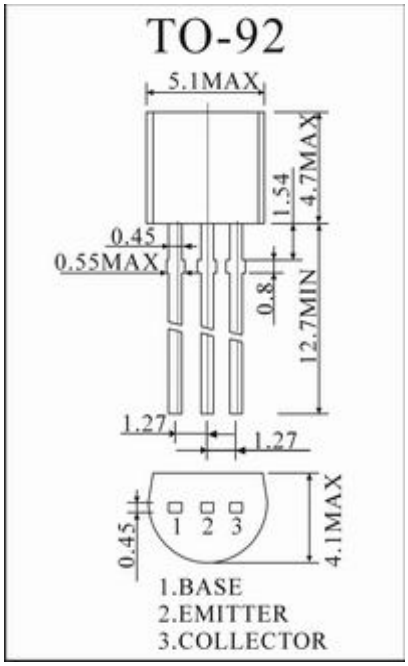
GuangDong Yuejing High Technology CO.,LTD.

C2062

—NPN silicon —

■■**APPLICATION**：High-Gain Amplifier.

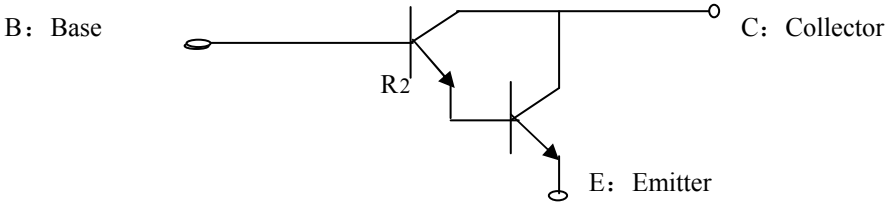


■■**MAXIMUM RATING**（Ta＝25℃）

PARAMETER	SYMBOL	RATING	UNIT
Collector-base voltage	V_{CBO}	40	V
Collector-emitter voltage	V_{CEO}	30	V
Emitter-base voltage	V_{EBO}	10	V
Collector current	I_C	300	mA
Collector Power Dissipation	P_C	300	mW
Junction Temperature	T_J	150	℃
Storage Temperature Range	Tstg	－55~150	℃

■■ **ELECTRICAL CHARACTERISTICS**（Ta=25℃）

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITION
Common Emitter DC Current Gain	h_{FE}	10K				V_{CE}= 3 V，Ic=100 mA
Collector Cut-off Current	I_{CBO}			0.1	μA	V_{CB}= 30 V，I_E=0
Emitter Cut-off Current	I_{EBO}			0.1	μA	V_{EB}= 10 V，Ic=0
Collector-Base Breakdown Voltage	BV_{CBO}	40			V	Ic= 0.1 mA，I_E=0
Collector-Emitter Breakdown Voltage	BV_{CEO}	30			V	Ic= 10 mA，I_B=0
Emitter-Base Breakdown Voltage	BV_{EBO}	10			V	I_E= 0.1mA，Ic=0
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$			1	V	Ic= 100 mA，I_B= 0.1 mA
Gain bandwidth product	f_T		200		MHz	Ic= 10 mA，V_{CE}= 5 V， f = 100 MHz
Common Base Output Capacitance	Cob		3.5		PF	V_{CB}= 30 V， I_E=0， f = 1 MHz



■■h_{FE} **Classification**

Classification	
h_{FE}	4000~20K